



CMBT3904E NPN
CMBT3906E PNP

**ENHANCED SPECIFICATION
COMPLEMENTARY FEMTOmini™
SILICON TRANSISTORS**

**ENHANCED
SPECIFICATION**

FEMTOmini™



SOT-923 CASE

FEATURES

- Very Small Package Size
- 200mA Collector Current
- Low $V_{CE(SAT)}$ (0.1V Typ @ 50mA)
- Miniature 0.8 x 0.6 x 0.4mm
- Ultra Low height profile
- **FEMTOmini™** Surface Mount Package

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

◆ **Collector-Base Voltage**

Collector-Emitter Voltage

◆ **Emitter-Base Voltage**

Collector Current

Power Dissipation

Operating and Storage

Junction Temperature

Thermal Resistance

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMBT3904E (NPN) and CMBT3906E (PNP) are general purpose transistors with enhanced specifications. These devices are ideal for applications where ultra small size and power dissipation are the prime requirements. Packaged in the **FEMTOmini™** SOT-923 package, these transistors provide performance characteristics suitable for the most demanding size constrained applications.

MARKING CODES: CMBT3904E: B
CMBT3906E: G

APPLICATIONS

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered applications including:
Cell Phones, Digital Cameras, Pagers,
PDAs, Laptop Computers, etc.

SYMBOL		UNITS
V_{CBO}	60	V
V_{CEO}	40	V
V_{EBO}	6.0	V
I_C	200	mA
P_D	100	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Θ_{JA}	1250	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	NPN			UNITS
		MIN	Typ	PNP	
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$			50	nA
◆ BV_{CBO}	$I_C=10\mu\text{A}$	60	115	90	V
BV_{CEO}	$I_C=1.0\text{mA}$	40	60	55	V
◆ BV_{EBO}	$I_E=10\mu\text{A}$	6.0	7.5	7.9	V
◆ $V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.057	0.050	V
◆ $V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.100	0.100	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.650	0.750	0.750	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.850	0.850	V

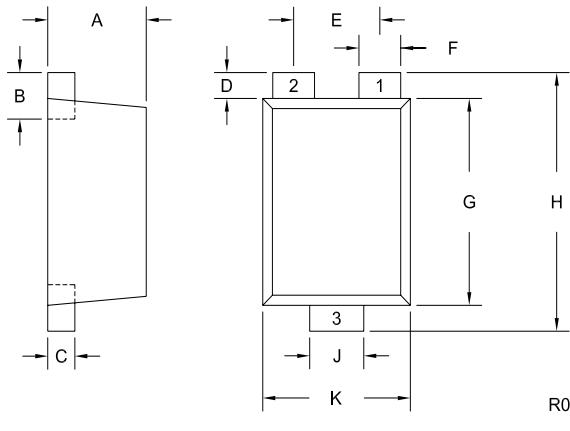
◆ Enhanced specification.

ELECTRICAL CHARACTERISTICS (continued)

SYMBOL	TEST CONDITIONS	MIN	NPN TYP	PNP TYP	MAX	UNITS
♦ h_{FE}	$V_{CE}=1.0V, I_C=0.1mA$	90	240	130		
♦ h_{FE}	$V_{CE}=1.0V, I_C=1.0mA$	100	235	150		
h_{FE}	$V_{CE}=1.0V, I_C=10mA$	100	215	150	300	
♦ h_{FE}	$V_{CE}=1.0V, I_C=50mA$	70	110	120		
h_{FE}	$V_{CE}=1.0V, I_C=100mA$	30	50	55		
f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300				MHz
C_{ob}	$V_{CB}=5.0V, I_E=0, f=1.0MHz$				4.0	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$				8.0	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			12	kΩ
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	0.1			10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	100			400	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			60	μmhos
NF	$V_{CE}=5.0V, I_C=100\mu A, R_S = 1.0k\Omega,$ $f=10Hz \text{ to } 15.7kHz$				4.0	dB
t_d	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_B1=1.0mA$				35	ns
t_r	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_B1=1.0mA$				35	ns
t_s	$V_{CC}=3.0V, I_C=10mA, I_B1=I_B2=1.0mA$				200	ns
t_f	$V_{CC}=3.0V, I_C=10mA, I_B1=I_B2=1.0mA$				50	ns

♦ Enhanced specification.

SOT-923 - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.015	0.016	0.39	0.41
B	0.004	0.010	0.10	0.26
C	0.003	0.006	0.08	0.14
D	0.002	0.006	0.05	0.15
E	0.014		0.35	
F	0.005	0.009	0.12	0.22
G	0.030	0.033	0.75	0.85
H	0.035	0.043	0.90	1.10
J	0.007	0.011	0.17	0.27
K	0.022	0.026	0.55	0.65

SOT-923 (REV: R0)

LEAD CODE:

- 1) BASE
- 2) Emitter
- 3) Collector